Part Number	Customer

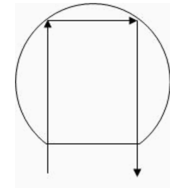
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	semi std	
	5.0	Overall Thickness	400.00 +/- 3.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<2.00µm	Guaranteed by Process
	7.0	Bow	<40.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<40.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	400.00 +/- 10.00 µm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Any	Wafer Vendor
	16.0	Handle Resistivity	0.005 ~ 0.02 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with lasermarking	Wafer Vendor
	18.0	Total LPD Count	< 30 pcs @ 0.3um	Tencor 6220 Surfscan
	19.0	Total scratch length	none	Tencor 6220 Surfscan, 100% bright light inspection
	20.0	Surface Haze	none	Tencor 6220 Surfscan, 100% bright light inspection
OverallWafer	21.0	Frontsurface condition	Surface roughness <5nm	Guaranteed by process

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

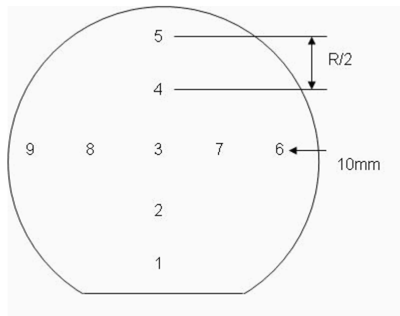
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information